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SEMICONDUCTOR



ESD



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GDT



PLED

BSZ130N03LS-MS

Product specification

Description

The BSZ130N03LS-MS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

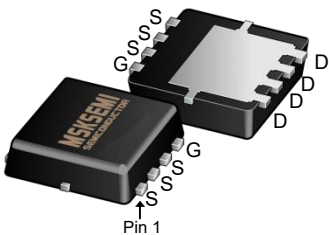
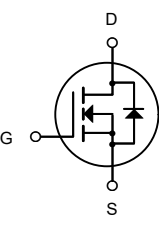

Features

- $V_{DS} = 30V$ $I_D = 30A$
- $R_{DS(ON)} < 13m\Omega$ @ $V_{GS}=10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Reference News

DFN3X3-8L	N-Channel MOSFET	Marking
		

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	30	A
$I_D @ T_c=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	18	A
I_{DM}	Pulsed Drain Current ²	55	A
E_{AS}	Single Pulse Avalanche Energy ³	22.1	mJ
I_{AS}	Avalanche Current	21	A
$P_D @ T_c=25^\circ C$	Total Power Dissipation ⁴	20	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	6	$^\circ C/W$

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25℃ , I _D =1mA	---	0.022	---	V/℃
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =10A	---	9	13	mΩ
		V _{GS} =4.5V , I _D =5A	---	12	20	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-5.1	---	mV/℃
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25℃	---	---	1	uA
		V _{DS} =24V , V _{GS} =0V , T _J =55℃	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V , I _D =1A	---	4.5	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.5	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V , V _{GS} =4.5V , I _D =10A	---	7.2	---	nC
Q _{gs}	Gate-Source Charge		---	1.4	---	
Q _{gd}	Gate-Drain Charge		---	2.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =12V , V _{GS} =10V , R _G =3.3 I _D =5A	---	4.1	---	ns
T _r	Rise Time		---	9.8	---	
T _{d(off)}	Turn-Off Delay Time		---	15.5	---	
T _f	Fall Time		---	6.0	---	
C _{iss}	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	572	---	pF
C _{oss}	Output Capacitance		---	81	---	
C _{rss}	Reverse Transfer Capacitance		---	65	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	28	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	55	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25℃	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=21A
- 4 .The power dissipation is limited by 150℃ junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications , should be limited by total power dissipation.

Typical Characteristics

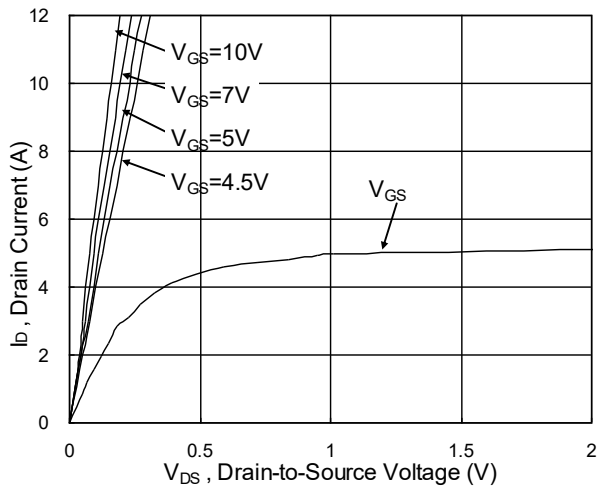


Fig.1 Typical Output Characteristics

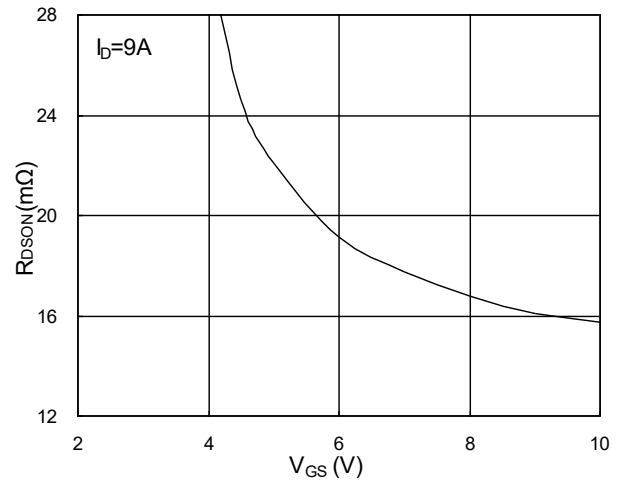


Fig.2 On-Resistance vs. Gate-Source

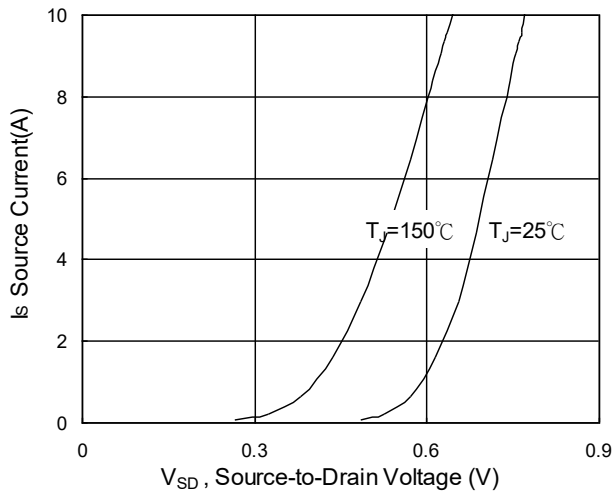


Fig.3 Forward Characteristics Of Reverse

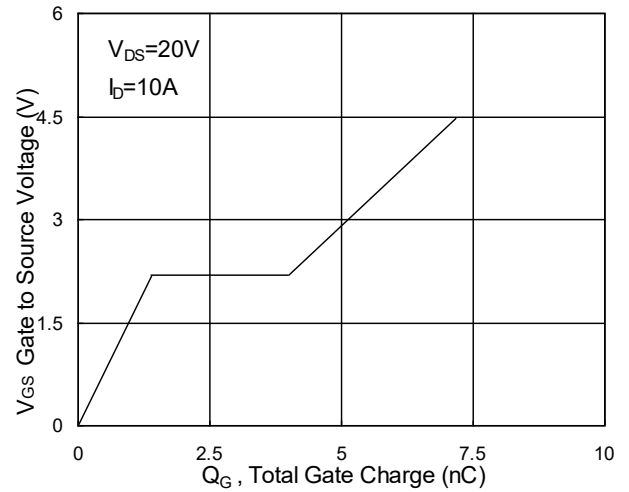


Fig.4 Gate-Charge Characteristics

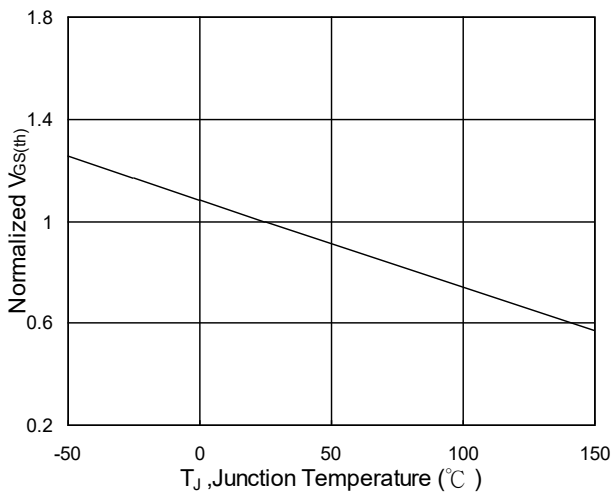


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

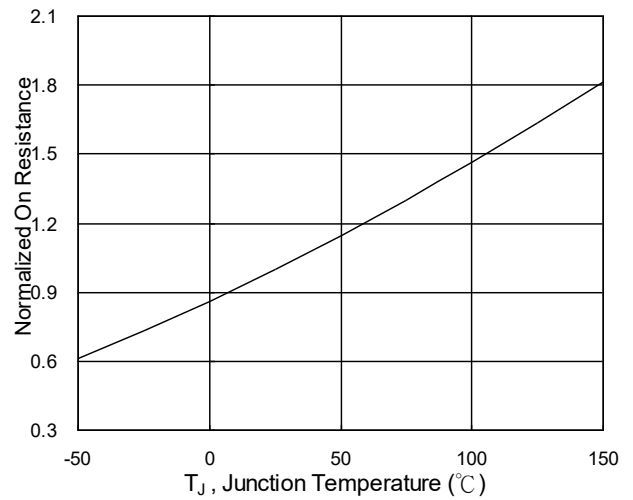


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

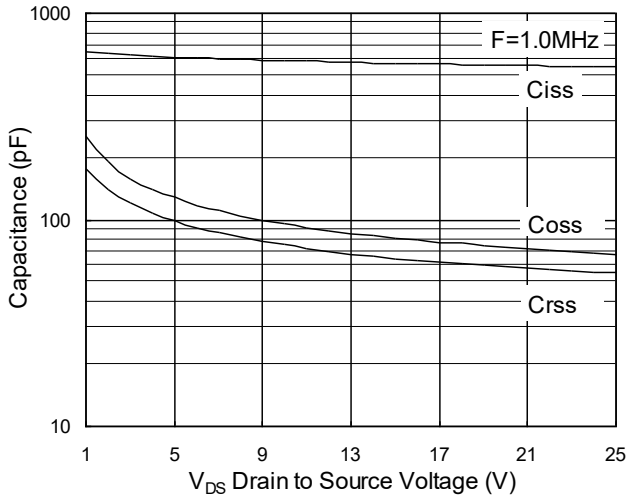


Fig.7 Capacitance

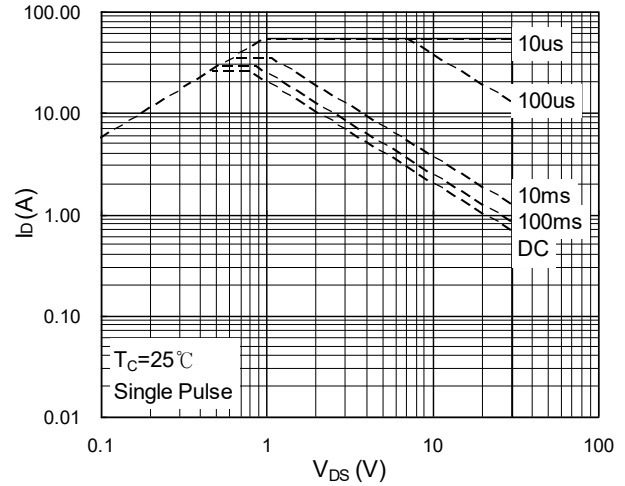


Fig.8 Safe Operating Area

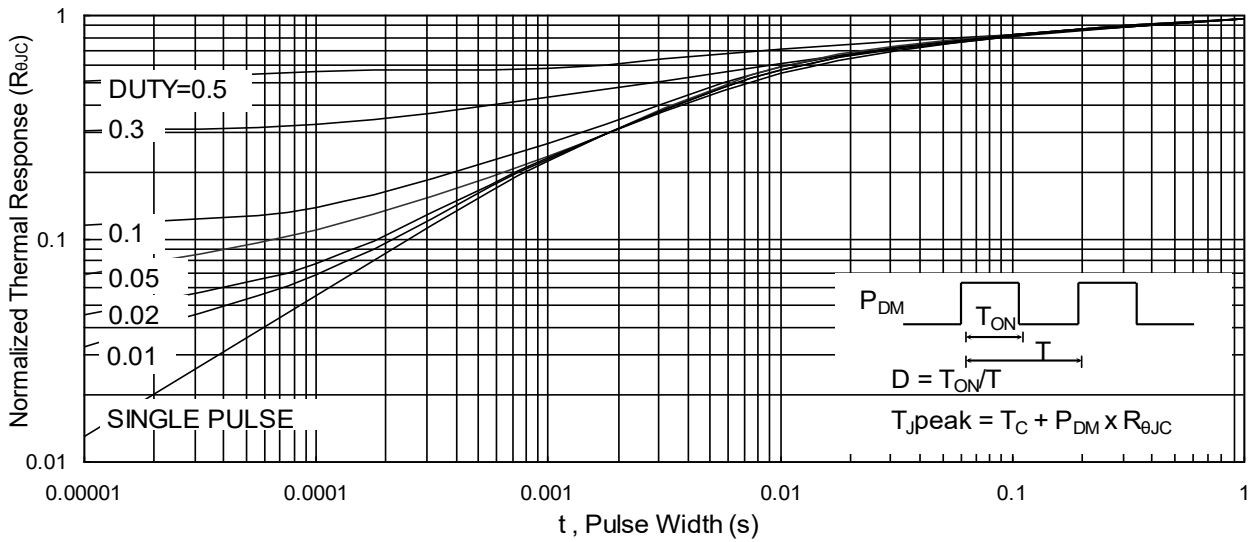


Fig.9 Normalized Maximum Transient Thermal Impedance

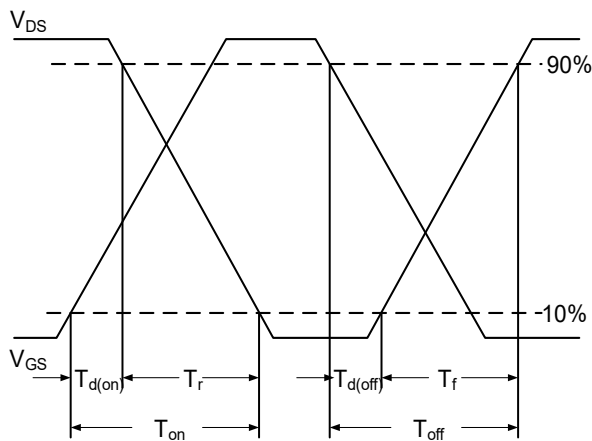


Fig.10 Switching Time Waveform

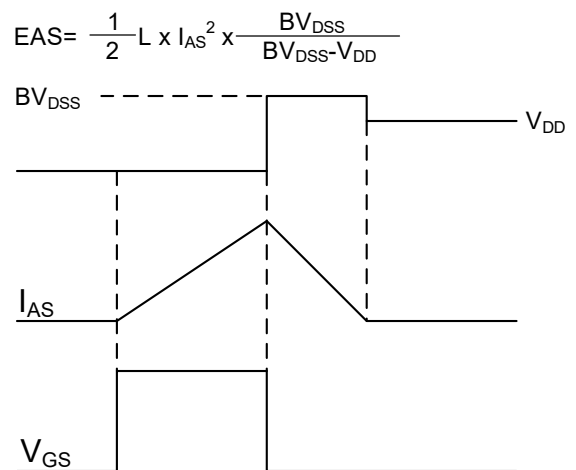
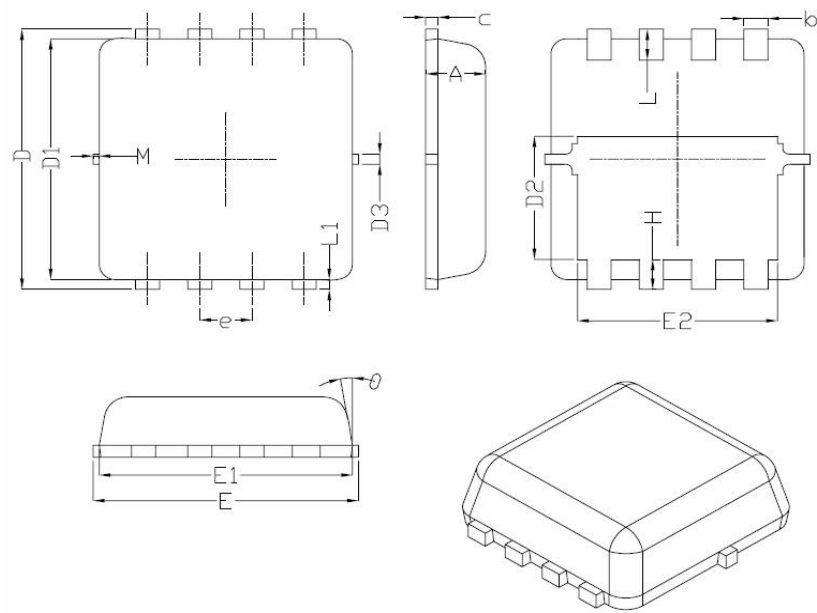


Fig.11 Unclamped Inductive Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

REEL SPECIFICATION

P/N	PKG	QTY
BSZ130N03LS-MS	DFN3X3-8L	5000

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